

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
60V	13mΩ@10V	25A
	16mΩ@4.5V	

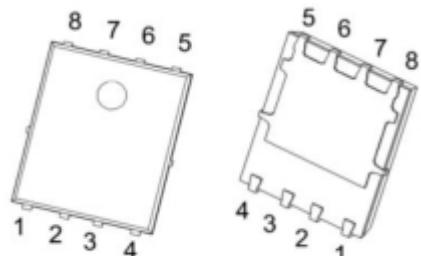
Feature

- Fast switching speed
- Surface mount package
- Reliable and Rugged
- ROHS Compliant & Halogen-Free

Applications

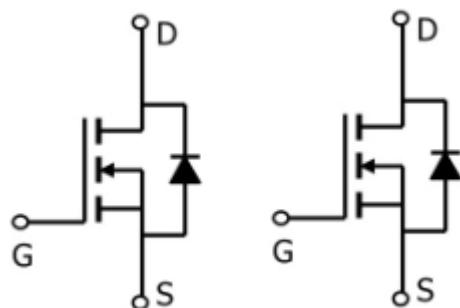
- DC-DC Converters.
- Motor Control.

Package



PDFNWB5X6-8L

Circuit diagram





ZL MOSFET

ZL60N13GD

Marking



60N13GD =Device Code
* =Month Code

Absolute maximum ratings

($T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current($T_c=25^\circ\text{C}$)	I_D	25	A
Pulse Drain Current Tested	I_{DM}	100	A
Maximum Power Dissipation($T_c=25^\circ\text{C}$)	P_D	73	W
Thermal Resistance-Junction to Case	$R_{\theta JC}$	1.71	$^\circ\text{C}/\text{W}$
Maximum Junction Temperature	T_J	-55 to 150	$^\circ\text{C}$
Storage Temperature Range	T_{STG} ,	-55 to 150	$^\circ\text{C}$



ZL MOSFET

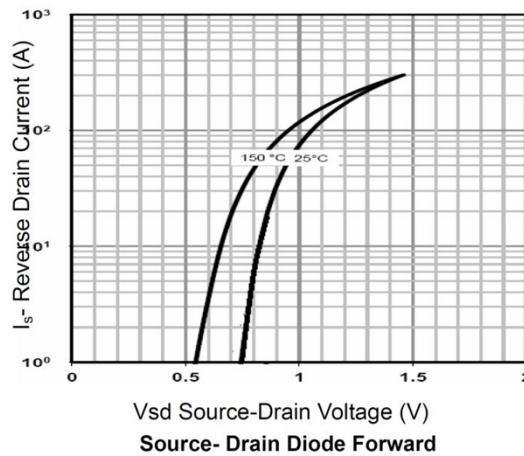
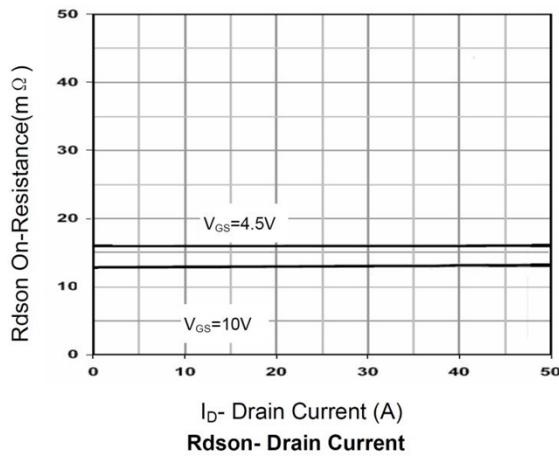
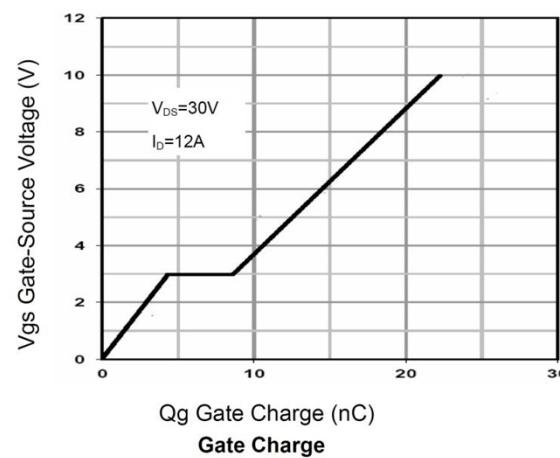
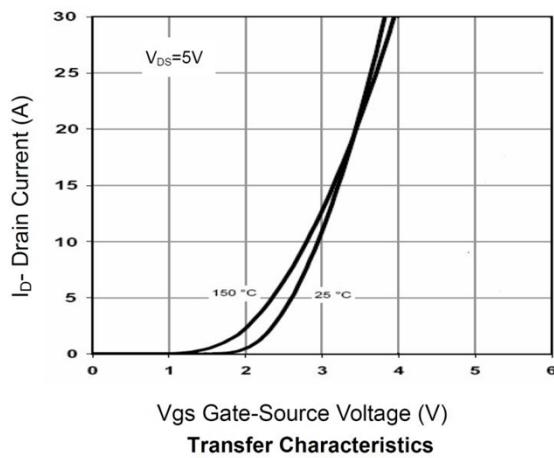
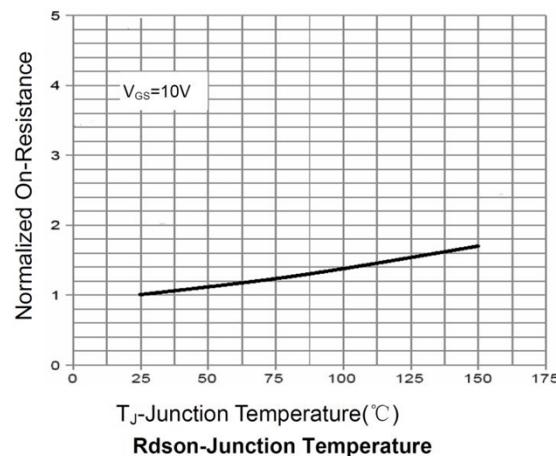
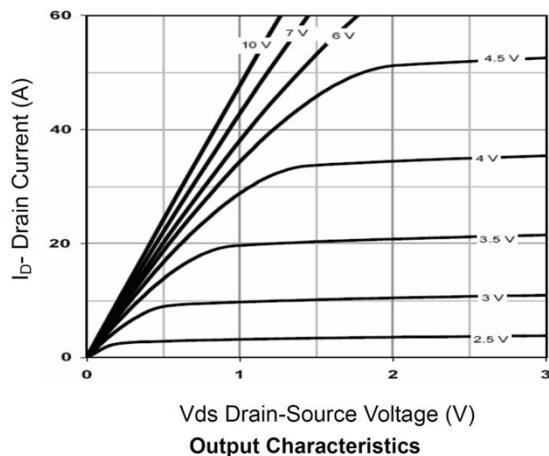
ZL60N13GD

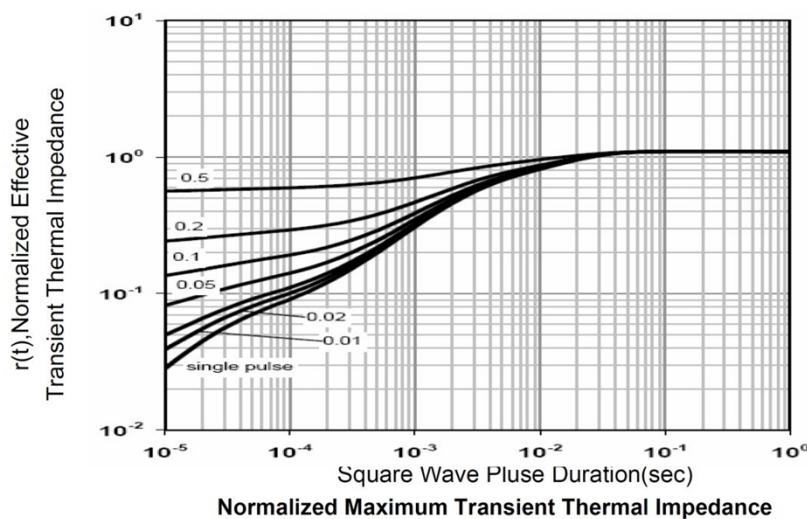
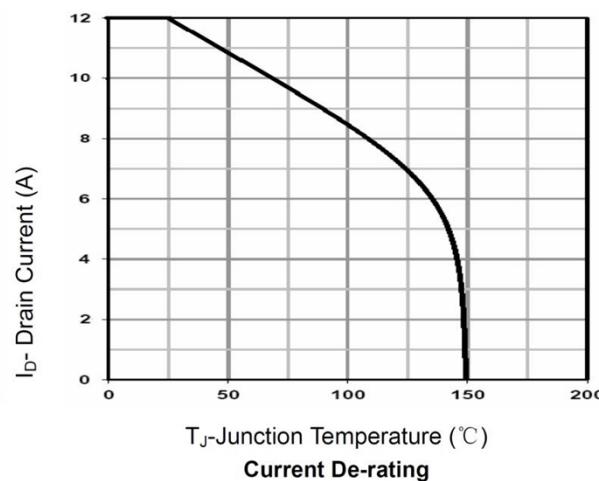
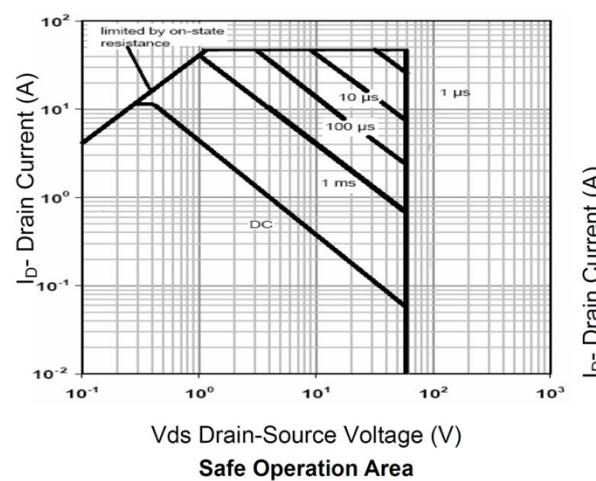
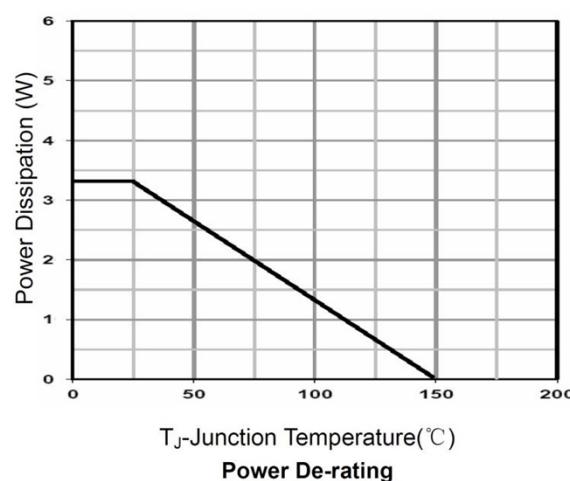
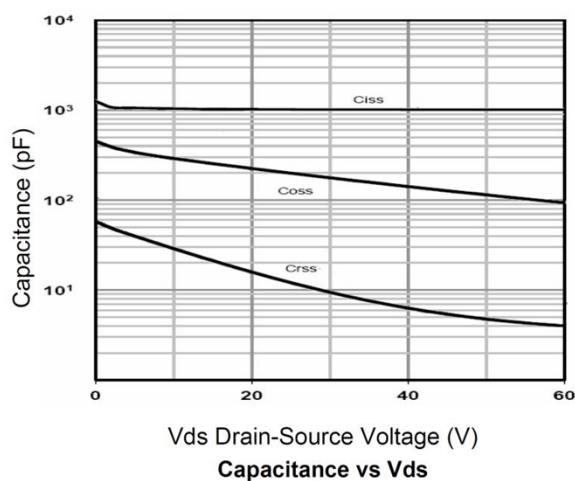
Electrical characteristics

(T_A=25°C, unless otherwise noted)

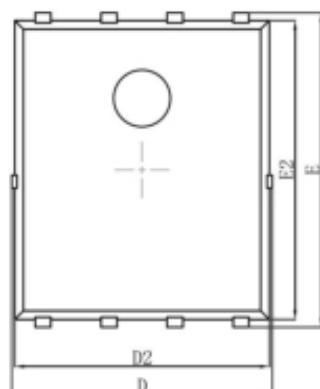
Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	BV _{(BR)DSS}	V _{GS} = 0V, I _D = 250μA	60			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 60V, V _{GS} = 0V			1	uA
Gate-Body Leakage Current	I _{GSS}	V _{GS} = ±20V, V _{DS} = 0V			±100	uA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250μA	1	1.8	2.5	V
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} = 10V, I _D = 10A		13	16	mΩ
		V _{GS} = 4.5V, I _D = 10A		16	21	
Dynamic and Switching Characteristics						
Input capacitance	C _{iss}	V _{GS} =0V, V _{DS} =30V, f=1MHz		426		pF
Output capacitance	C _{oss}			103		
Reverse transfer capacitance	C _{rss}			8		
Turn-on Delay Time	T _{d(on)}	V _{DD} =30V, I _D = 10A, V _{GS} =10V, R _G = 1.6Ω		8		nS
Turn-on Rise Time	T _r			5		
Turn-Off Delay Time	T _{d(off)}			24		
Turn-Off Fall Time	t _f			3.5		
Total Gate Charge	Q _g	V _{DS} =30V , V _{GS} =10V, I _D = 10A		35		pF
Gate-Source Charge	Q _{gs}			6.4		
Gate-Drain Charge	Q _{gd}			3.5		
Drain-Source Body Diode Characteristics						
Diode Forward Voltage	V _{SD}	V _{GS} =0V , I _S =1A			1.2	V

Typical Characteristics

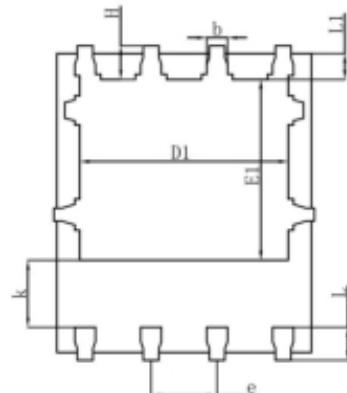




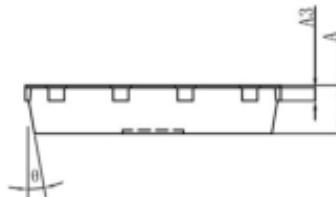
PDFNWB5X6-8L Package Information



Top View
[顶视图]



Bottom View
[背视图]



Side View
[侧视图]

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.000	0.035	0.039
A3	0.254REF.		0.010REF.	
D	4.944	5.096	0.195	0.201
E	5.974	6.126	0.235	0.241
D1	3.910	4.110	0.154	0.162
E1	3.375	3.575	0.133	0.141
D2	4.824	4.976	0.190	0.196
E2	5.674	5.826	0.223	0.229
k	1.190	1.390	0.047	0.055
b	0.350	0.450	0.014	0.018
e	1.270TYP.		0.050TYP.	
L	0.559	0.711	0.022	0.028
L1	0.424	0.576	0.017	0.023
H	0.574	0.726	0.023	0.029
θ	10°		12°	